

## Product Overview

### NV BG080N120SC1: Silicon Carbide MOSFET, N-Channel, 1200 V, 80 mΩ , D2PAK-7L

For complete documentation, see the data sheet.

Silicon Carbide (SiC) MOSFET uses a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size.

#### Features

- Qualified for Automotive According to AEC-Q101
- 1200V rated
- High Speed Switching and Low Capacitance
- 100% UIL Tested
- Devices are RoHS Compliant

#### Benefits

- Automotive Grade

#### Applications

- High power DCDC
- Inverter

#### End Products

- Automotive DC/DC converter for EV/PHEV
- Automotive Inverters

Part Electrical Specifications													
Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	Blocking Voltage BV <sub>DSS</sub> (V)	I <sub>D(max)</sub> (A)	R <sub>DS(on)</sub> Typ @ 25°C (mΩ)	Q <sub>G Total</sub> (C)	Output Capacitance (C)	T <sub>J Max</sub> (°C)	Package Type	
NV BG080N120SC1	5.9999	AEC Qualified PPAP Capable Pb-free Halide free	NEW	N-Channel	Single	1200	30	80	56	79	175	D2PAK7 (TO-263-7L HV)	

For more information please contact your local sales support at [www.onsemi.com](http://www.onsemi.com).

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